NSN 5962-01-202-4662

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low level

View Online at https://aerobasegroup.com/nsn/5962-01-202-4662

Body L	enath.
0.840 ir	-
Body V	
-	n 0.220 inches and 0.310 inches
Body H	
0.185 ir	
	Im Power Dissipation Rating:
794.0 m	
	ng Tempurature Range:
	25.0 degrees celsius
	e Tempurature Range:
	50.0 degrees celsius
	plication:
	et an/sps-52c
	s Provided:
Bipolar	and programmed and schottky and w/active pull-up and 3-state output
	re Material:
Cerami	or glass or metal
	re Configuration:
Dual-in-	line
Output	Logic Form:
	or-transistor logic
Input C	ircuit Pattern:
10 inpu	
Case O	utline Source And Designator:
D-2 mil	m-38510
Termin	al Surface Treatment:
Solder	
Voltage	Rating And Type Per Characteristic:
-0.5 vol	s power source and 7.0 volts power source
Time R	ating Per Chacteristic:
85.00 n	anoseconds propagation delay time, low to high level output and 85.00 nanoseconds propagation delay time, high to l
output	
Memor	/ Device Type:
Prom	
Memor	/ Capacity:
Unknov	n
Test Da	ta Document:
96906-ı	nil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Termin	al Type And Quantity:
16 print	ed circuit
Shelf L	fe:
N/a	

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Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A458a0

